



STV160NF03L

N - CHANNEL 30V - 0.0016Ω - 160A - PowerSO-10 STripFET™ MOSFET

TYPE	V _{DSS}	R _{DS(on)}	I _D
STV160NF03L	30 V	< 0.0025 Ω	160 A

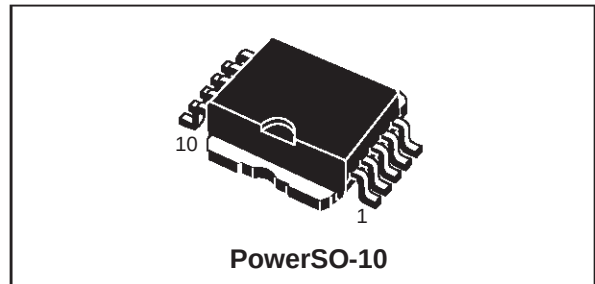
- TYPICAL R_{DS(on)} = 0.0016 Ω
- ULTRA LOW ON-RESISTANCE
- ULTRA FAST SWITCHING
- 100% AVALANCHE TESTED
- VERY LOW GATE CHARGE
- LOW THRESHOLD DRIVE
- LOW PROFILE, VERY LOW PARASITIC INDUCTANCE PowerSO-10 PACKAGE

DESCRIPTION

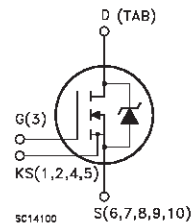
The **STV160NF03L** represents the second generation of Application Specific STMicroelectronics well established STripFET™ process based on a very unique strip layout design. The resulting MOSFET shows unrivalled high packing density with ultra low on-resistance and superior switching characteristics. Process simplification also translates into improved manufacturing reproducibility. This device is particularly suitable for high current, low voltage switching application where efficiency is crucial.

APPLICATIONS

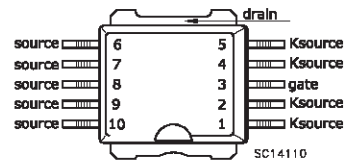
- BUCK CONVERTERS IN HIGH PERFORMANCE TELECOM AND VRMs
- DC-DC CONVERTERS



INTERNAL SCHEMATIC DIAGRAM



CONNECTION DIAGRAM (TOP VIEW)



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{DS}	Drain-source Voltage (V _{GS} = 0)	30	V
V _{DGR}	Drain- gate Voltage (R _{GS} = 20 kΩ)	30	V
V _{GS}	Gate-source Voltage	± 20	V
I _D (**)	Drain Current (continuous) at T _c = 25 °C	160	A
I _D	Drain Current (continuous) at T _c = 100 °C	113	A
I _{DM} (•)	Drain Current (pulsed)	640	A
P _{tot}	Total Dissipation at T _c = 25 °C	160	W
	Derating Factor	1.07	W/°C
T _{stg}	Storage Temperature	-65 to 175	°C
T _j	Max. Operating Junction Temperature	175	°C

(•) Pulse width limited by safe operating area

(**) Limited only maximum junction temperature allowed by PowerSO-10

THERMAL DATA

$R_{thj-case}$	Thermal Resistance Junction-case	Max	0.9375	$^{\circ}C/W$
$R_{thj-amb}$	Thermal Resistance Junction-ambient	Max	50	$^{\circ}C/W$
T_l	Maximum Lead Temperature For Soldering Purpose		300	$^{\circ}C$

ELECTRICAL CHARACTERISTICS ($T_J = 25^{\circ}C$ unless otherwise specified)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source Breakdown Voltage	$I_D = 250 \mu A$ $V_{GS} = 0$	30			V
I_{DSS}	Zero Gate Voltage Drain Current ($V_{GS} = 0$)	$V_{DS} = \text{Max Rating}$ $V_{DS} = \text{Max Rating}$ $T_c = 25^{\circ}C$			1 10	μA μA
I_{GSS}	Gate-body Leakage Current ($V_{DS} = 0$)	$V_{GS} = \pm 15 V$			± 100	nA

ON (*)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}$ $I_D = 250 \mu A$ $T_c = 25^{\circ}C$	1	1.7	2.5	V
$R_{DS(on)}$	Static Drain-source On Resistance	$V_{GS} = 10V$ $I_D = 80 A$ $V_{GS} = 8V$ $I_D = 80 A$ $V_{GS} = 4.5V$ $I_D = 40 A$ $V_{GS} = 10V$ $I_D = 80 A$ $T_J = 175^{\circ}C$ $V_{GS} = 8V$ $I_D = 80 A$ $T_J = 175^{\circ}C$ $V_{GS} = 4.5V$ $I_D = 40 A$ $T_J = 175^{\circ}C$		1.6 1.7 3.5	2.5 3.5 6 5.7 7 11.4	m Ω m Ω m Ω m Ω m Ω m Ω
$I_{D(on)}$	On State Drain Current	$V_{DS} > I_{D(on)} \times R_{DS(on)max}$ $V_{GS} = 10 V$	160			A

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$g_{fs} (*)$	Forward Transconductance	$V_{DS} > I_{D(on)} \times R_{DS(on)max}$ $I_D = 80 A$		210		S
R_g	Gate resistance	$V_{DS} = 15 V$ $f = 1 MHz$ $V_{GS} = 0$		0.9		Ω
C_{iss} C_{oss} C_{rss}	Input Capacitance Output Capacitance Reverse Transfer Capacitance	$V_{DS} = 15 V$ $f = 1 MHz$ $V_{GS} = 0$		4900 2950 565		pF pF pF
C_{iss} C_{oss} C_{rss}	Input Capacitance Output Capacitance Reverse Transfer Capacitance	$V_{DS} = 0 V$ $f = 1 MHz$ $V_{GS} = 0$		7200 13000 4220		pF pF pF

ELECTRICAL CHARACTERISTICS (continued)**SWITCHING ON**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on Delay Time	$V_{DD} = 15\text{ V}$ $I_D = 40\text{ A}$		23		ns
t_r	Rise Time	$R_G = 4.7\ \Omega$ $V_{GS} = 10\text{ V}$ (Resistive Load, see fig. 3)		350		ns
Q_g	Total Gate Charge	$V_{DD} = 16\text{ V}$ $I_D = 160\text{ A}$ $V_{GS} = 10\text{ V}$		103		nC
Q_{gs}	Gate-Source Charge			38		nC
Q_{gd}	Gate-Drain Charge			9		nC

SWITCHING OFF

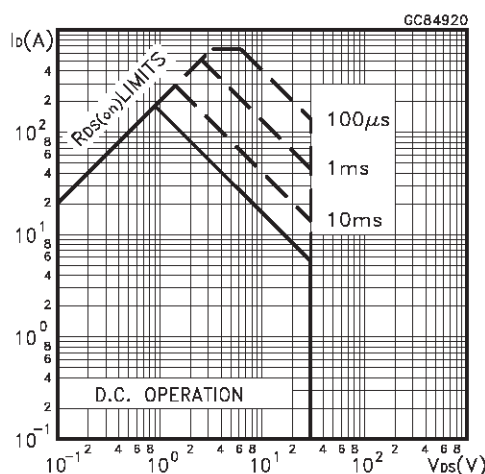
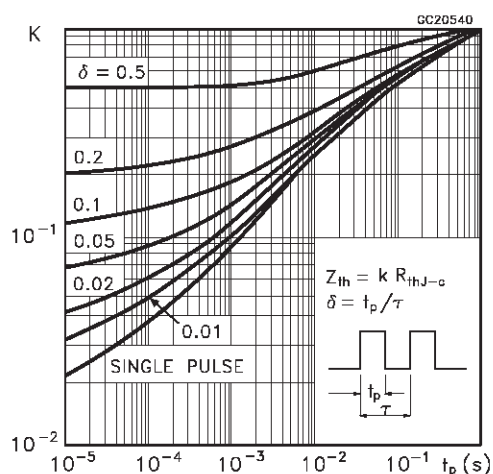
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(off)}$	Turn-off Delay Time	$V_{DD} = 15\text{ V}$ $I_D = 40\text{ A}$		105		ns
t_f	Fall Time	$R_G = 4.7\ \Omega$ $V_{GS} = 10\text{ V}$ (Resistive Load, see fig. 3)		120		ns
$t_{d(off)}$	Turn-off Delay Time	$V_{clamp} = 16\text{ V}$ $I_D = 80\text{ A}$		85		ns
$t_{r(voff)}$	Off-voltage Rise Time	$R_G = 4.7\ \Omega$ $V_{GS} = 10\text{ V}$		46		ns
t_f	Fall Time	(Inductive Load, see fig. 5)		335		ns
t_c	Cross-over Time			404		ns

SOURCE DRAIN DIODE

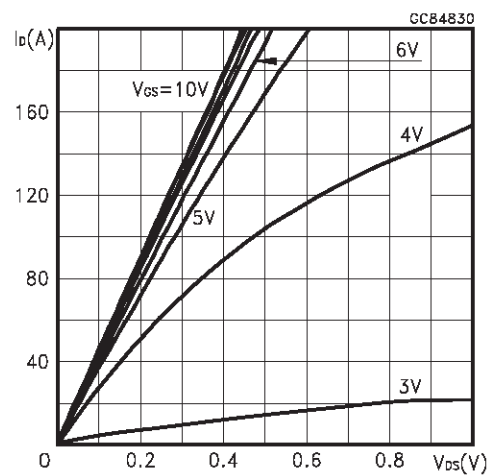
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain Current				160	A
$I_{SDM}(\bullet)$	Source-drain Current (pulsed)				640	A
$V_{SD} (*)$	Forward On Voltage	$I_{SD} = 160\text{ A}$ $V_{GS} = 0$			1.5	V
t_{rr}	Reverse Recovery Time	$I_{SD} = 80\text{ A}$ $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 15\text{ V}$ (see test circuit, fig. 5)		100		ns
Q_{rr}	Reverse Recovery Charge			0.25		μC
I_{RRM}	Reverse Recovery Current			5		A

(*) Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %

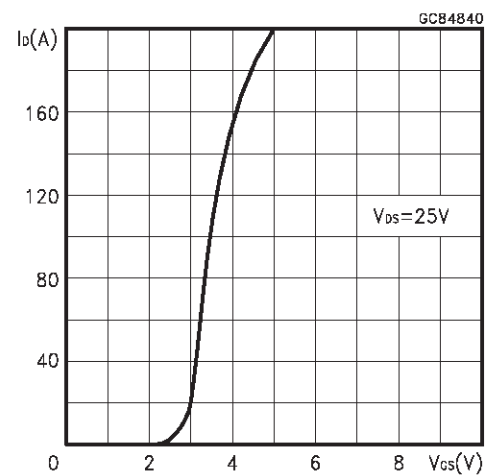
(\bullet) Pulse width limited by safe operating area

Safe Operating Area**Thermal Impedance**

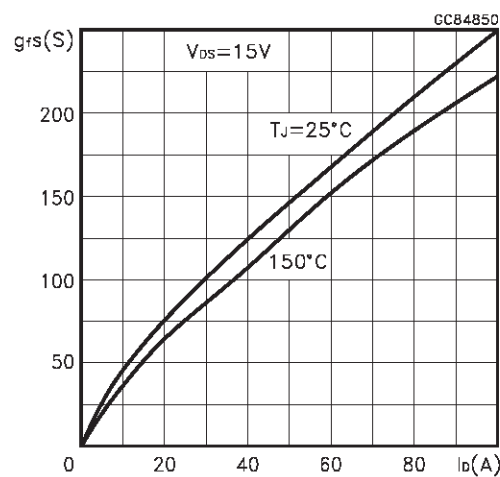
Output Characteristics



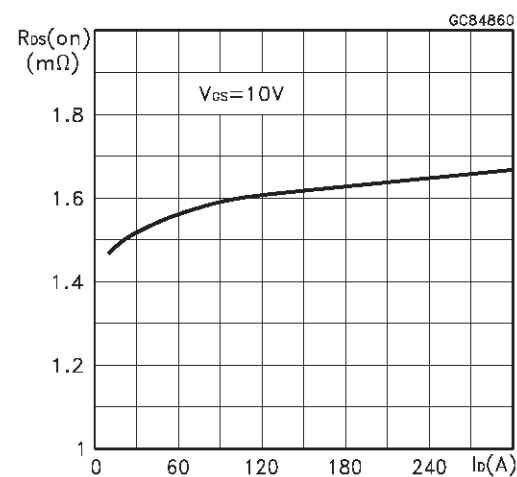
Transfer Characteristics



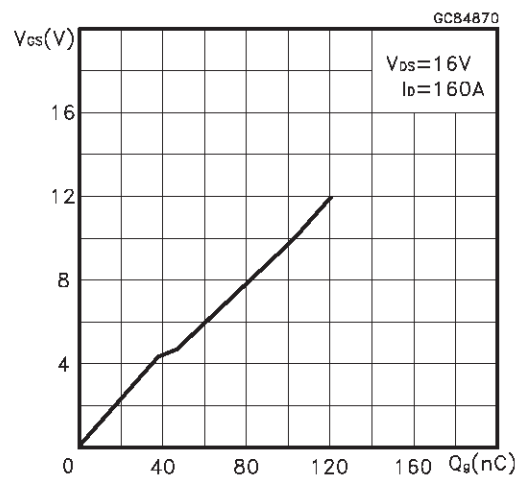
Transconductance



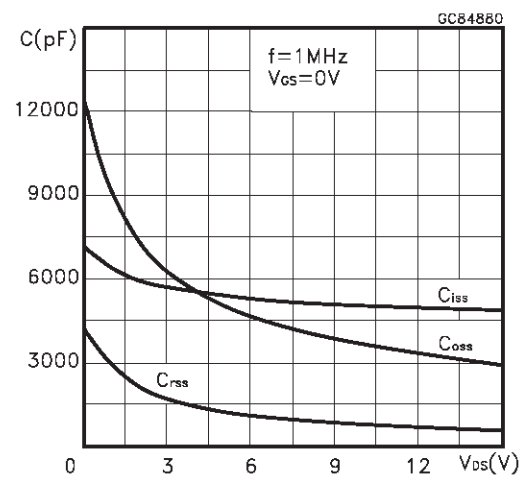
Static Drain-source On Resistance



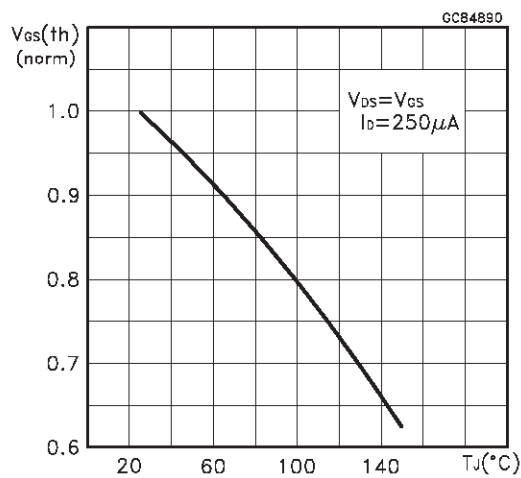
Gate Charge vs Gate-source Voltage



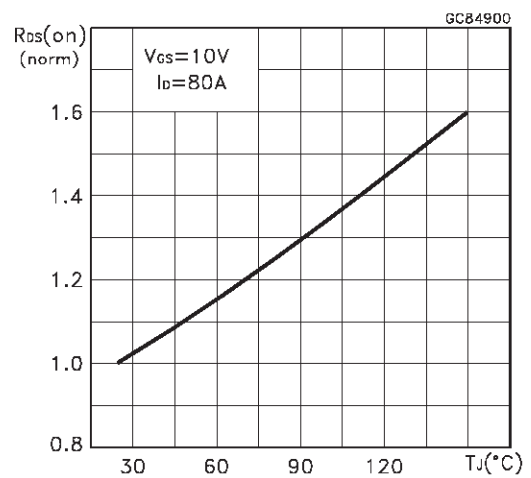
Capacitance Variations



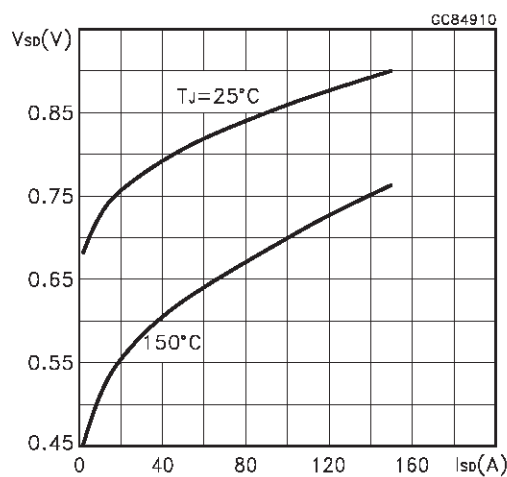
Normalized Gate Threshold Voltage vs Temperature



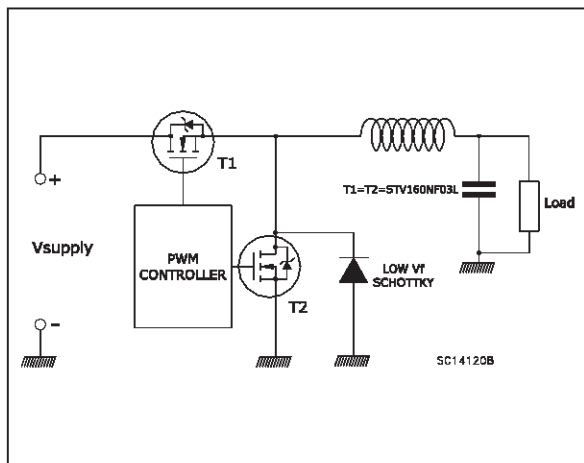
Normalized On Resistance vs Temperature



Source-drain Diode Forward Characteristics



Basic Schematic For Motherboard VRM With Synchronous Rectification



Basic Schematic Mosfet Switch Used In Secondary Side Of a Foward Convert

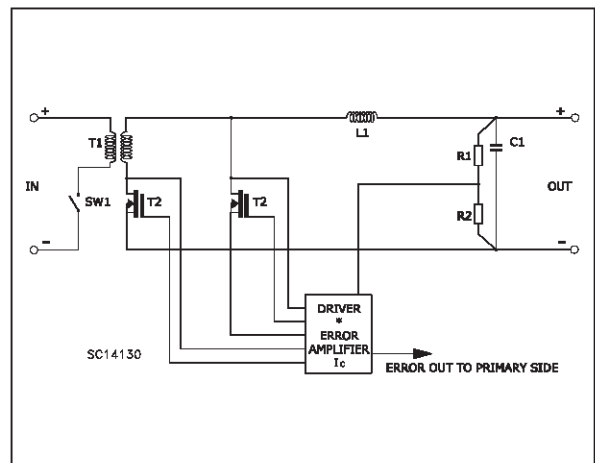


Fig. 1: Unclamped Inductive Load Test Circuit

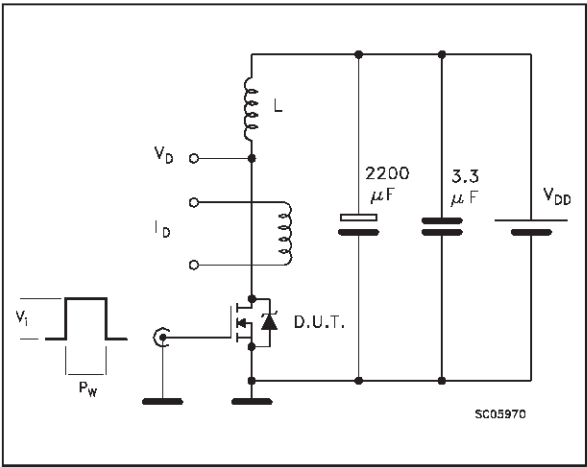


Fig. 2: Unclamped Inductive Waveform

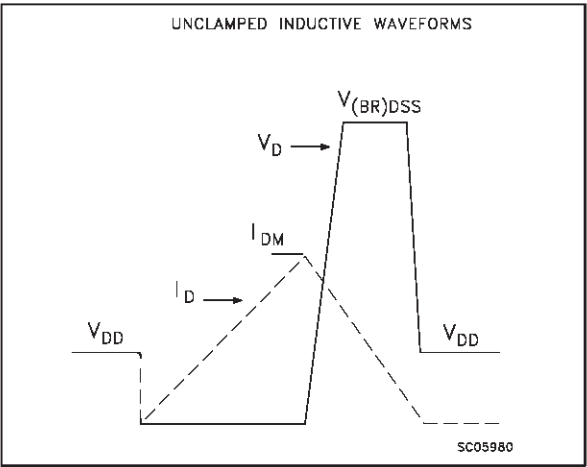


Fig. 3: Switching Times Test Circuits For Resistive Load

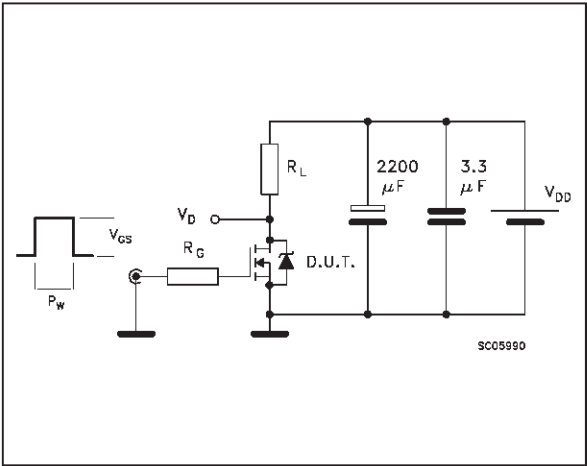


Fig. 4: Gate Charge test Circuit

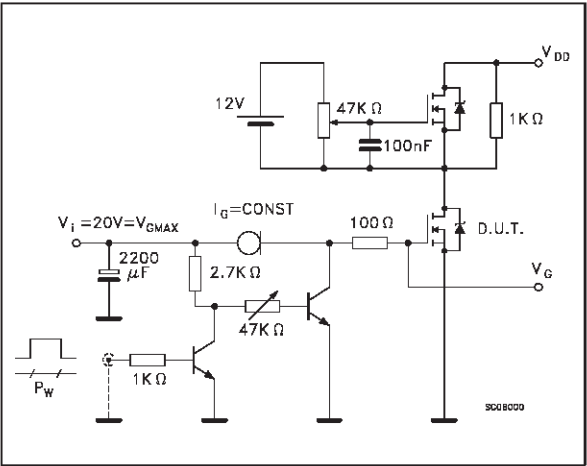
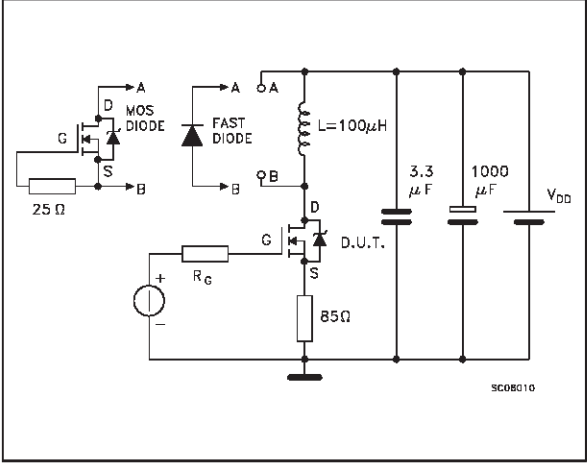
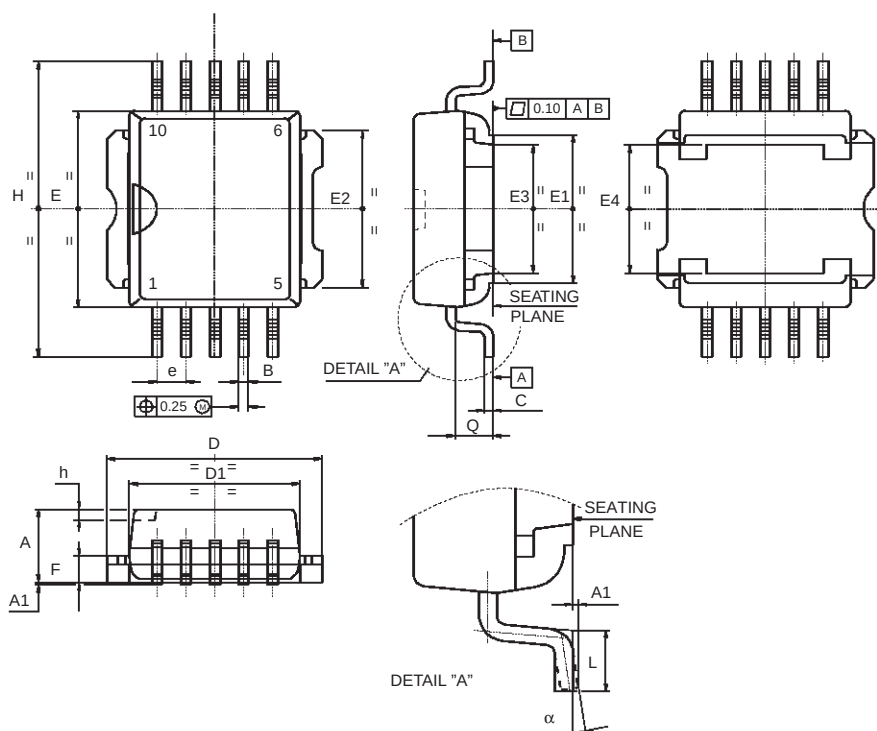


Fig. 5: Test Circuit For Inductive Load Switching And Diode Recovery Times



PowerSO-10 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	3.35		3.65	0.132		0.144
A1	0.00		0.10	0.000		0.004
B	0.40		0.60	0.016		0.024
c	0.35		0.55	0.013		0.022
D	9.40		9.60	0.370		0.378
D1	7.40		7.60	0.291		0.300
E	9.30		9.50	0.366		0.374
E1	7.20		7.40	0.283		0.291
E2	7.20		7.60	0.283		0.300
E3	6.10		6.35	0.240		0.250
E4	5.90		6.10	0.232		0.240
e		1.27			0.050	
F	1.25		1.35	0.049		0.053
H	13.80		14.40	0.543		0.567
h		0.50			0.002	
L	1.20		1.80	0.047		0.071
q		1.70			0.067	
α	0°		8°			



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